

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	539545	gate	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:48
L2	62580	1 and (gate near5 (dielectric oxide insualt\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:48
L3	19344	2 and spacer	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:48
L4	2805	3 and (ONO (oxide near10 nitrde near10 oxide))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:49
L5	2755	4 and (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:51
L6	2537	5 and (dop\$3 implant)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:52
L7	1716	6 and ((conductive polysilicon silicon) near20 spacer)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:35
L8	992	7 and (control near5 gate)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:35
L9	903	8 and (float\$3 near5 gate)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:53
L10	573	9 and ((bit word) near5 line)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:36
L11	575	9 and ((bit word) near10 line)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:36
L12	575	11 10	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/30 18:36
L13	476493	gate	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/30 18:48
L14	9956	13 and spacer	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/30 18:48

L15	4530	14 and (gate near5 (dielectric oxide insualt\$3))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/30 18:49
L16	62	15 and (ONO (oxide near10 nitrde near10 oxide))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/30 18:49
L17	2979	15 and (etch\$3 pattern\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/30 18:51
L18	1354	17 and (dop\$3 implant)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/30 18:52
L19	157	18 and ((float\$3 control) near5 gate)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/30 18:53